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FODM121 Series, FODM124, FODM2701, FODM2705 4-Pin Full Pitch Mini-Flat Package Phototransistor Optocouplers

Features

- More than 5 mm Creepage/Clearance
- Compact 4-Pin Surface Mount Package (2.4 mm Maximum Standoff Height)
- Current Transfer Ratio in Selected Groups: DC Input: FODM121: 50–600%

FODM121A: 100–300% FODM121B: 50–150% FODM121C: 100–200% FODM124: 100% MIN FODM2701: 50–300% AC Input: FODM2705: 50–300%

- Safety and Regulatory Approvals:
 - UL1577, 3,750 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

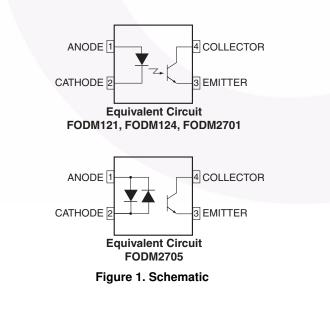
Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver

Description

The FODM121 series, FODM124, and FODM2701 consists of a gallium arsenide infrared emitting diode driving a phototransistor in a compact 4-pin mini-flat package. The lead pitch is 2.54 mm. The FODM2705 consists of two gallium arsenide infrared emitting diodes connected in inverse parallel for AC operation.

Functional Block Diagram



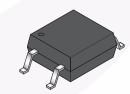


Figure 2. Package Outlines

November 2015

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	I–III	
Climatic Classification		40/110/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	904	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1 \text{ s}$, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 5	mm
	External Clearance	≥ 5	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ _S	Case Temperature ⁽¹⁾	150	°C
I _{S,INPUT}	Input Current ⁽¹⁾	200	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	300	mW
R _{IO}	Insulation Resistance at T_S , V_{IO} = 500 $V^{(1)}$	> 10 ⁹	Ω

Note:

1. Safety limit values - maximum values allowed in the event of a failure.

Absolute Maximum Ratings

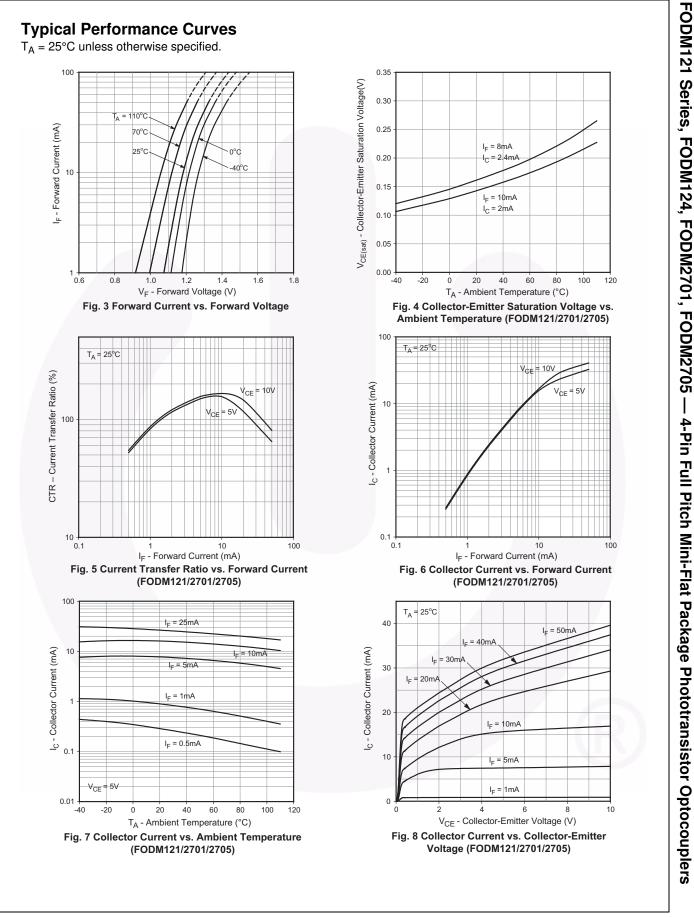
Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ Unless otherwise specified.

Symbol	Parar	neter	Value	Unit
TOTAL PACKA	IGE		I	
T _{STG}	Storage Temperature		-40 to +125	°C
T _{OPR}	Operating Temperature		-40 to +110	°C
TJ	Junction Temperature		-40 to +125	°C
T _{SOL}	Lead Solder Temperature		260 for 10 sec	°C
EMITTER			·	
I _{F (avg)}	Continuous Forward Current		50	mA
I _{F (pk)}	Peak Forward Current (1 µs puls	1	А	
V _R	Reverse Voltage		6	V
Р	Power Dissipation		70	mW
PD	Derate linearly (Above 75°C)		1.41	mW/°C
DETECTOR				
Ι _C	Continuous Collector Current		80	mA
V		FODM121 Series, FODM124	80	V
V _{CEO}	Collector-Emitter Voltage	FODM2701, FODM2705	40	v
V _{ECO}	Emitter-Collector Voltage		6	V
D	Power Dissipation		150	mW
PD	Derate linearly (Above 80°C)		3.27	mW/°C

	Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit	
$ V_{F} Forward Voltage \begin{cases} FODM121 Series, FODM124 \\ FODM2701 \\ FODM2705 \\ Fer = 15 mA \\ \hline FODM2705 \\ Fer = 15 mA \\ \hline FODM2705 \\ Fer = 15 mA \\ \hline FODM121 Series, FODM121 \\ FODM2701 \\ \hline FODM2705 \\ \hline F = 15 mA, V_{CE} = 5 V \\ \hline S0 \\ \hline FODM121 \\ \hline FODM1210 \\ \hline F = 10 mA, V_{CE} = 5 V \\ \hline S0 $	INDIVIDU	AL COMPONENT CHAR	ACTERISTICS						
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Emitter								
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$.,	-		I _F = 10 mA	1.0		1.3		
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	V _F	Forward Voltage	FODM2701	I _F = 5 mA			1.4	V	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			FODM2705	I _F = ±5 mA					
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	I _R	Reverse Current	FODM124,	V _R = 5 V			5	μA	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Detecto	r							
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	BV	Collector-Emitter		-1 m A - 0	80			V	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	D CEO	Breakdown Voltage	,	C = 1 mA, $F = 0$	40			V	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	BV _{ECO}		All	$I_{E} = 100 \ \mu A, \ I_{F} = 0$	7			v	
TRANSFER CHARACTERISTICS CTR FODM2701 $I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ 50 300 FODM2705 $I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$ 50 300 FODM1210 $FODM121A$ $I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ 50 600 FODM121B $FODM121B$ $I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ 50 100 300 FODM121C $FODM121C$ $I_F = 1 \text{ mA}, V_{CE} = 0.5 \text{ V}$ 100 1200 FODM124 $I_F = 1 \text{ mA}, V_{CE} = 0.5 \text{ V}$ 100 1200 FODM124 $I_F = 1 \text{ mA}, V_{CE} = 0.5 \text{ V}$ 100 1200 VCE(SAT) Saturation Voltage FODM121 Series $I_F = 8 \text{ mA}, I_C = 2.4 \text{ mA}$ 0.4 FODM2701 $I_F = 10 \text{ mA}, I_C = 0.5 \text{ mA}$ 0.4 0.3 FODM2705 $I_F = 10 \text{ mA}, I_C = 2 \text{ mA}$ 0.3 0.3 Rise Time All $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ 3 0.3	I _{CEO}	Collector Dark Current	All	$V_{CE} = 40 \text{ V}, I_{F} = 0$			100	nA	
$ CTR \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	C _{CE}	Capacitance	All	$V_{CE} = 0 V, f = 1 MHz$		10		pF	
$ CTR \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	TRANSFE	ER CHARACTERISTICS							
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			FODM2701	$I_{F} = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50		300		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			FODM2705	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	50		300		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			FODM121		50		600		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	CTR	DC Current Transfer	FODM121A	1 - 5 m $1 - 5 V$	100		300	%	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	OIII	Ratio	FODM121B	$v_{\text{CE}} = 0$ mA, $v_{\text{CE}} = 0$ v	50		150	/0	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			FODM121C		100		200		
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$				$I_{F} = 1 \text{ mA}, V_{CE} = 0.5 \text{ V}$	100		1200		
$V_{CE(SAT)} = \frac{FODM121 \text{ Series}}{Saturation \text{ Voltage}} = \frac{FODM121 \text{ Series}}{FODM124} = \frac{I_F = 8 \text{ mA}, I_C = 2.4 \text{ mA}}{I_F = 1 \text{ mA}, I_C = 0.5 \text{ mA}} = \frac{0.4}{0.4}$ $\frac{FODM2701}{FODM2701} = \frac{I_F = 10 \text{ mA}, I_C = 2 \text{ mA}}{I_F = 10 \text{ mA}, I_C = 2 \text{ mA}} = \frac{0.3}{0.3}$ $\frac{I_F = 10 \text{ mA}, I_C = 2 \text{ mA}}{I_F = \pm 10 \text{ mA}, I_C = 2 \text{ mA}} = \frac{0.3}{0.3}$			1 ODW124	$I_{F} = 0.5 \text{ mA}, V_{CE} = 1.5 \text{ V}$	50				
$ V_{CE(SAT)} \begin{array}{ c c c c c c c c c c c c c c c c c c c$		CTR Symmetry	FODM2705	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$	0.3		3.0		
$\begin{array}{c c} V_{CE(SAT)} \\ \hline Saturation Voltage \\ \hline FODM2701 \\ \hline FODM2705 \\ \hline I_F = \pm 10 \text{ mA}, I_C = 2 \text{ mA} \\ \hline I_F = \pm 10 \text{ mA}, I_C = 2 \text{ mA} \\ \hline 0.3 \\ \hline $			FODM121 Series	$I_{\rm F} = 8 \text{ mA}, I_{\rm C} = 2.4 \text{ mA}$			0.4	- V	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		Saturation Voltage	FODM124	$I_{\rm F} = 1 {\rm mA}, I_{\rm C} = 0.5 {\rm mA}$			0.4		
$I_{\rm C} = 2 \text{ mA}, V_{\rm CE} = 5 \text{ V},$	♥CE(SAT)		FODM2701	$I_{\rm F} = 10 \text{ mA}, I_{\rm C} = 2 \text{ mA}$			0.3		
			FODM2705	$I_{F} = \pm 10 \text{ mA}, I_{C} = 2 \text{ mA}$			0.3		
	t _r	Rise Time (Non-Saturated)	All	$ I_C = 2 \text{ mA}, \text{V}_{CE} = 5 \text{ V}, \\ \text{R}_L = 100 \Omega $		3		μs	
$t_{f} \begin{cases} Fall Time \\ (Non-Saturated) \end{cases} All \begin{cases} I_{C} = 2 \text{ mA}, V_{CE} = 5 \text{ V}, \\ R_{L} = 100 \Omega \end{cases} 3 \end{cases}$	t _f		All			3		μs	
	ISO	Steady State Isolation Voltage ⁽²⁾	All	1 minute	3750			VAC _{RM}	

Note:

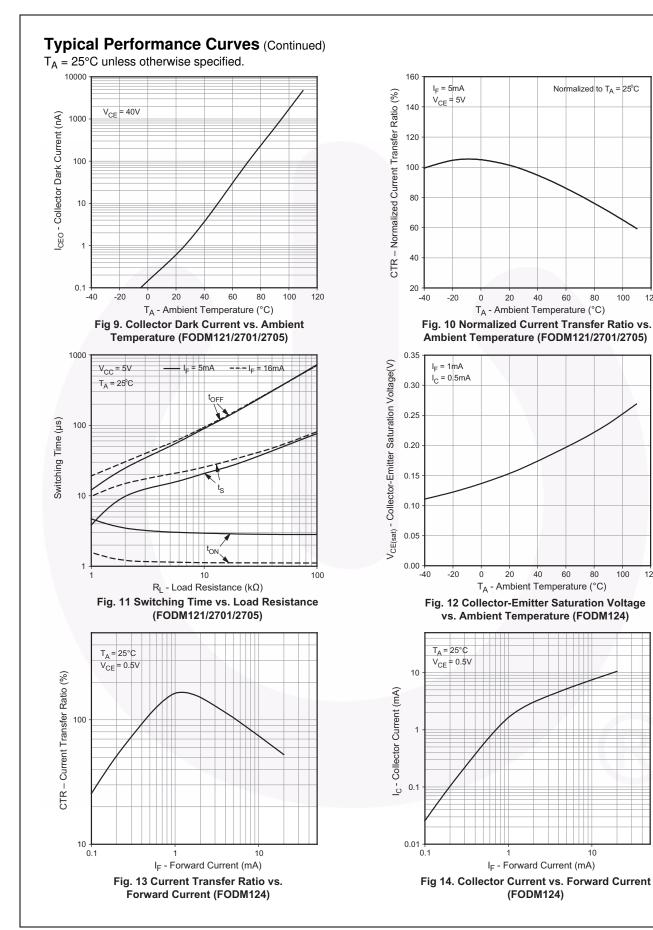
2. Steady state isolation voltage, V_{ISO}, is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 3 and 4 are common.

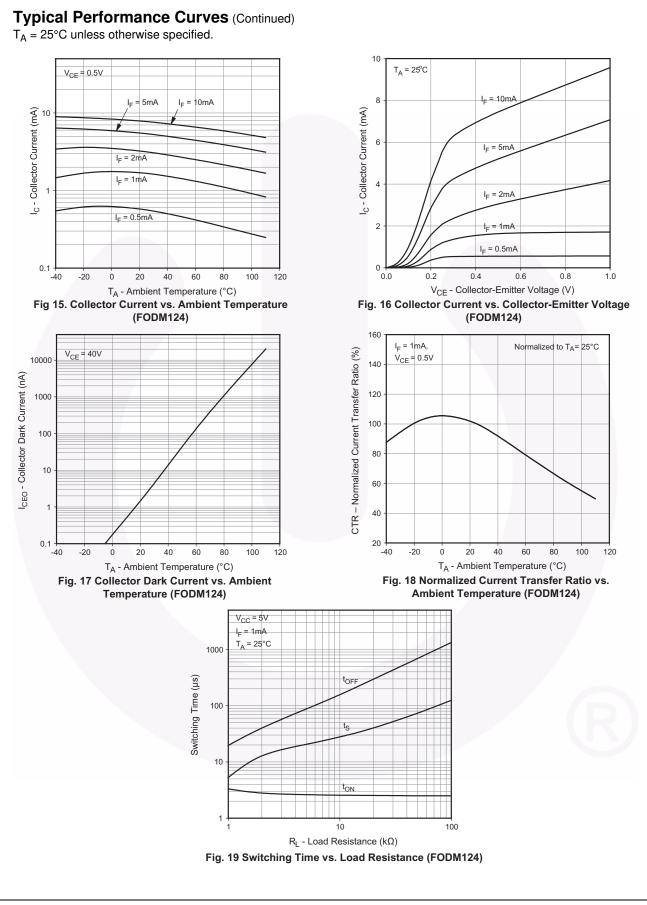


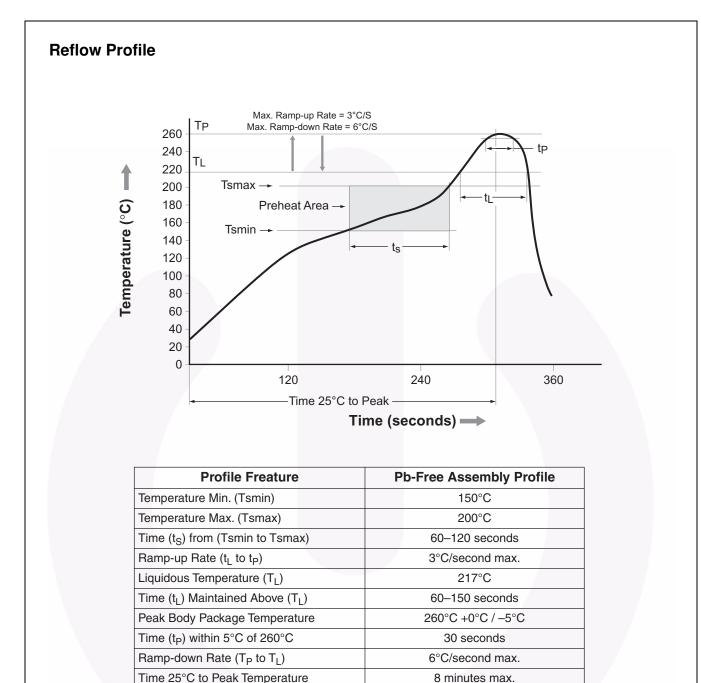


120

120







Ordering Information

Part Number	Package	Packing Method
FODM121	Full Pitch Mini-Flat 4-Pin	Tube (100 units)
FODM121R2	Full Pitch Mini-Flat 4-Pin	Tape and Reel (2500 Units)
FODM121V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
FODM121R2V	Full Pitch Mini-Flat 4-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

Note:

The product orderable part number system listed in this table also applies to the FODM121A, FODM121B, FODM121C, FODM124, FODM2701, and FODM2705 products.

Marking Information

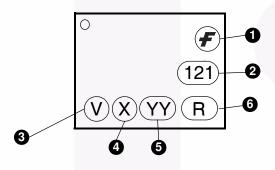
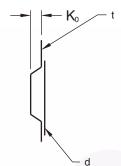


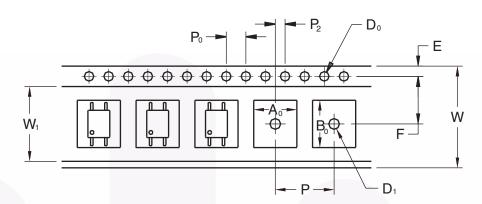
Figure 20. Top Mark

Table 1. Top Mark Definitions

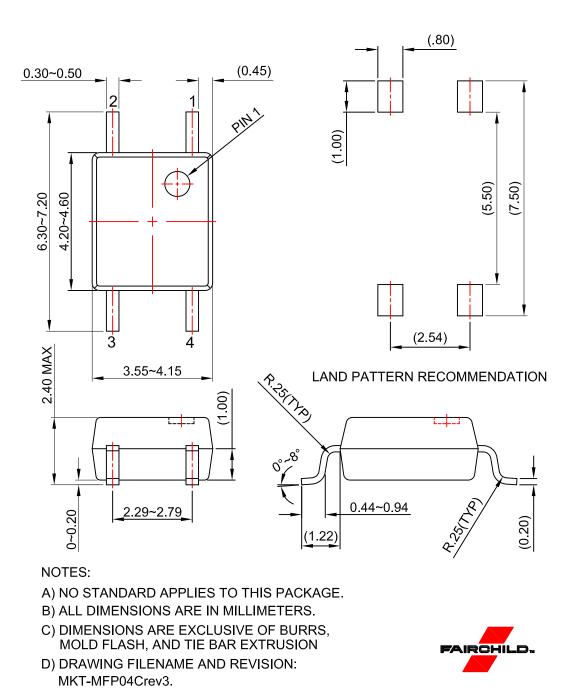
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "5"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code

Carrier Tape Specifications





		2.54 Pitch
Description	Symbol	Dimensions
Tape Width	W	12.00±0.4
Tape Thickness	t	0.35±0.02
Sprocket Hole Pitch	Po	4.00±0.20
Sprocket Hole Dia.	Do	1.55±0.20
Sprocket Hole Location	E	1.75±0.20
Pocket Location	F	5.50±0.20
	P ₂	2.00±0.20
Pocket Pitch	P	8.00±0.20
Pocket Dimension	A ₀	4.75±0.20
	B ₀	7.30±0.20
	K ₀	2.30±0.20
Pocket Hole Dia.	D ₁	1.55±0.20
Cover Tape Width	W1	9.20
Cover Tape Thickness	d	0.065±0.02
Max. Component Rotation or Tilt		20° max
Devices Per Reel		2500
Reel Diameter		330 mm (13")



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